

# SOT-23 Plastic-Encapsulate Transistors

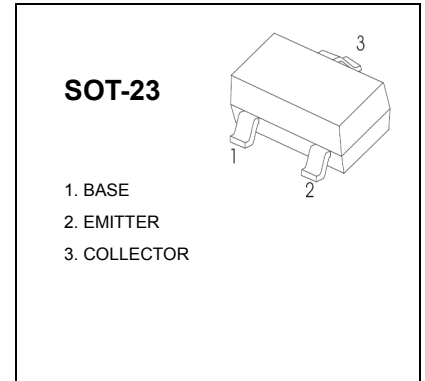
**MMBTA92** TRANSISTOR (PNP)

**FEATURES**

High voltage transistor

**MARKING:2D**

**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**



Symbol	Parameter	Value	Unit
<b>V<sub>CB0</sub></b>	Collector-Base Voltage	-300	V
<b>V<sub>CEO</sub></b>	Collector-Emitter Voltage	-300	V
<b>V<sub>EBO</sub></b>	Emitter-Base Voltage	-5	V
<b>I<sub>C</sub></b>	Collector Current -Continuous	-200	mA
<b>I<sub>CM</sub></b>	Collector Current -Pulsed	-500	mA
<b>P<sub>C</sub></b>	Collector Power Dissipation	300	mW
<b>T<sub>J</sub></b>	Junction Temperature	150	°C
<b>T<sub>stg</sub></b>	Storage Temperature	-55-150	°C
<b>R<sub>θJA</sub></b>	Thermal Resistance From Junction To Ambient	417	°C/W

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Max	Unit
<b>Collector-base breakdown voltage</b>	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-300		V
<b>Collector-emitter breakdown voltage</b>	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-300		V
<b>Emitter-base breakdown voltage</b>	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5		V
<b>Collector cut-off current</b>	$I_{CBO}$	$V_{CB} = -200V, I_E = 0$		-0.25	μA
<b>Emitter cut-off current</b>	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$		-0.1	μA
<b>DC current gain</b>	$h_{FE(1)}$	$V_{CE} = -10V, I_C = -1mA$	60		
	$h_{FE(2)}$	$V_{CE} = -10V, I_C = -10mA$	100	200	
	$h_{FE(3)}$	$V_{CE} = -10V, I_C = -30mA$	60		
<b>Collector-emitter saturation voltage</b>	$V_{CE(sat)}$	$I_C = -20mA, I_B = -2mA$		-0.2	V
<b>Base-emitter saturation voltage</b>	$V_{BE(sat)}$	$I_C = -20mA, I_B = -2mA$		-0.9	V
<b>Transition frequency</b>	$f_T$	$V_{CE} = -20V, I_C = -10mA$ $f = 30MHz$	50		MHz

# Typical Characteristics

